

IN THE CLAIMS:

Please ADD new claim 18, as follows. For the Examiner's convenience, all claims currently pending in this application have been reproduced below:

1-12. (Canceled)

13. (Previously Presented) An apparatus for forming a pattern, said apparatus comprising:

a photomask for light exposure provided with both a first aperture having a minute width where a main component of transmitted light is evanescent light and a second aperture having a larger width than that of said first aperture where a main component of transmitted light is propagating light;

a sample stand for placing a substrate to be processed on which a photoresist with a film thickness equal to or smaller than a width of the first aperture is formed;

a stage for placing the photomask;

a light source for generating light for exposure; and

means for controlling a distance between the substrate to be processed and the photomask,

wherein the width of said second aperture is smaller than a designed dimension of said photomask and the width of said second aperture is longer than a wavelength of light for exposure.

14. (Original) The apparatus according to claim 13, wherein the photomask comprises an elastic material as a mask material.

15. (Canceled)

16. (Previously Presented) The apparatus according to claim 13, wherein the width of said first aperture is shorter than a wavelength of light for exposure.

17. (Canceled)

18. (New) An apparatus for forming a pattern, said apparatus comprising:

a photomask for light exposure provided with both a first aperture having a minute width in which a main component of transmitted light is evanescent light and a second aperture having a larger width than that of the first aperture in which a main component of transmitted light is propagating light;

a sample stand for placing a substrate to be processed on which a photoresist is formed;

a stage for placing the photomask;  
a light source for generating light for exposure; and  
means for controlling a distance between the substrate to be processed and the photomask,

wherein the size of the second aperture is less than that of a pattern to be formed in the photoresist by developing the photoresist after exposure using the photomask, and the width of the second aperture is longer than a wavelength of light for exposure.